

NX6351GP Series

Data Sheet

LASER DIODE

1 270/1 290/1 310/1 330/1 350 nm AlGaInAs MQW-DFB LASER DIODE

FOR 9.8 Gb/s CPRI and 10G E-PON ONU APPLICATION

R08DS0087EJ0100

Rev.1.00

Feb 25, 2013

DESCRIPTION

The NX6351GP series is a 1 270/1 290/1 310/1 330/1 350 nm Multiple Quantum Well (MQW) structured Distributed Feed-Back (DFB) laser diode with InGaAs monitor PIN-PD.

APPLICATIONS

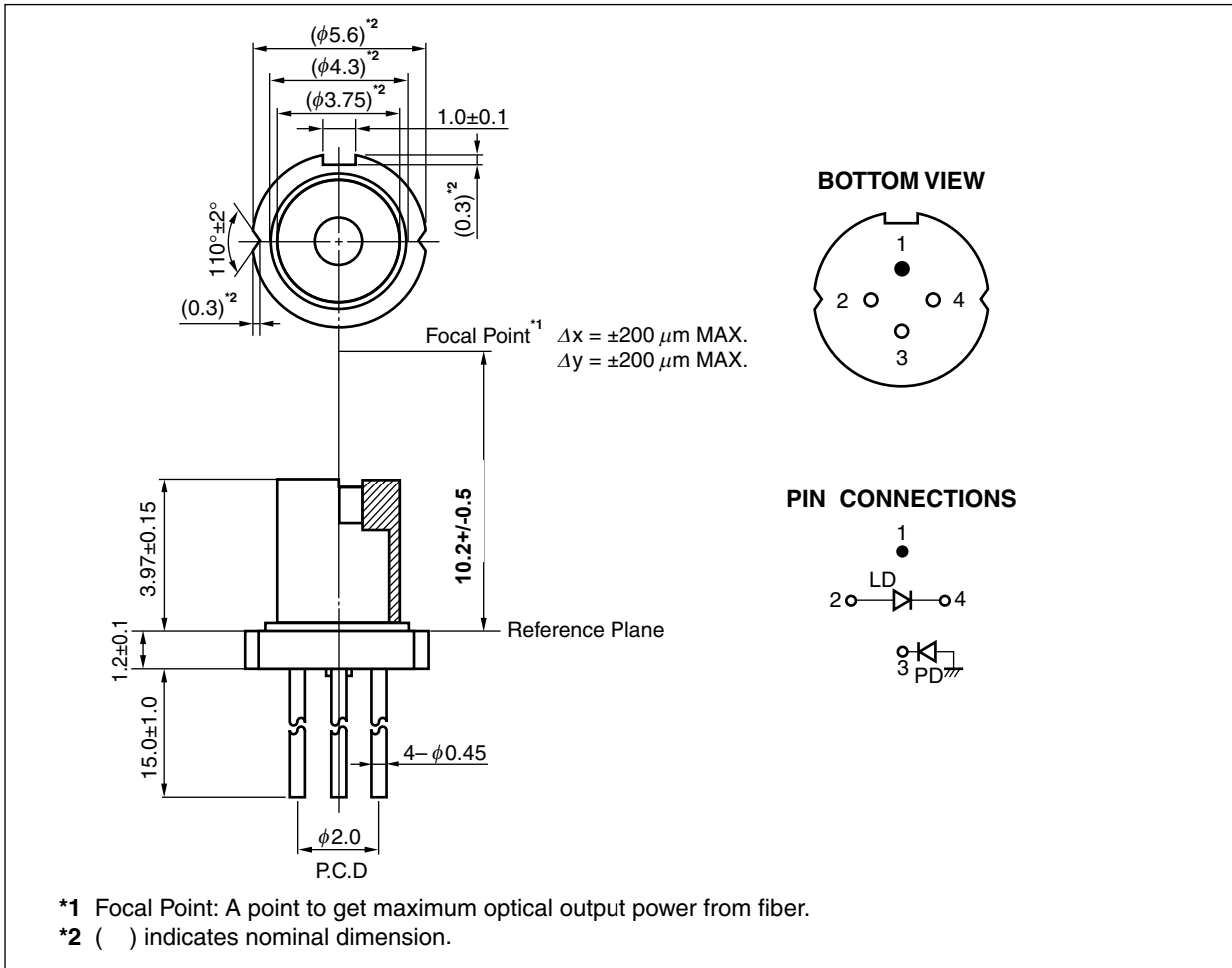
- 9.8 Gbps CPRI
- 10G E-PON ONU

FEATURES

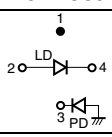
- | | |
|------------------------------------|---|
| • Optical output power | $P_O = 8.5 \text{ mW}$ |
| • Low threshold current | $I_{th} = 7 \text{ mA}$ |
| • Differential efficiency | $\eta_d = 0.35 \text{ W/A}$ |
| • Wide operating temperature range | $T_C = -40 \text{ to } +85^\circ\text{C}$ |
| • InGaAs monitor PIN-PD | |
| • CAN package | $\phi 5.6 \text{ mm}$ |
| • Focal point | 10.2 mm |



PACKAGE DIMENSIONS (UNIT: mm)



ORDERING INFORMATION

Part Number	Package	Pin Connections
NX6351GPxx*	TO-18	

Note: 1. The last two digits ("xx") of Part Number indicates Wavelength Code.
The relationships between the code and wavelength are as follows.

WAVELENGTH CODE	WAVELENGTH (nm)
27	1 270
29	1 290
31	1 310
33	1 330
35	1 350

Remarks 1. The color of lens cap might be observed differently.
2. The hermetic test will be performed as AQL 1.0%.

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Optical Output Power	P_O	15	mW
Forward Current of LD	I_F	120	mA
Reverse Voltage of LD	V_R	2.0	V
Forward Current of PD	I_F	10.0	mA
Reverse Voltage of PD	V_R	15	V
Operating Case Temperature	T_C	-40 to +85	$^\circ\text{C}$
Storage Temperature	T_{stg}	-40 to +95	$^\circ\text{C}$
Lead Soldering Temperature	T_{sld}	350 (3 sec.)	$^\circ\text{C}$
Relative Humidity (noncondensing)	RH	85	%

RECOMMENDED LD DRIVE CURRENT AT MODULE LEVEL

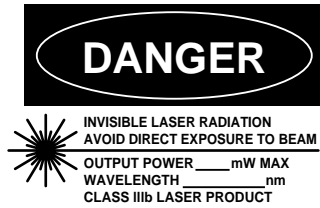
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Bias Current	I_{bias}	$T_C = 25^\circ\text{C}$	-	30	-	mA
		$T_C = 85^\circ\text{C}$	-	-	70	

ELECTRO-OPTICAL CHARACTERISTICS
($T_C = -40$ to $+85^\circ\text{C}$, CW, BOL, unless otherwise specified)

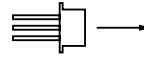
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit	
Signaling Rate			-	9.8304	-	Gb/s	
Optical Output Power	P_O		-	8.5	-	mW	
Operating Voltage	V_{op}	$P_O = 8.5$ mW	-	-	2.0	V	
Threshold Current	I_{th}	$T_C = 25^\circ\text{C}$	-	7	15	mA	
			-	-	30		
Differential Efficiency	η_d	$P_O = 8.5$ mW, $T_C = 25^\circ\text{C}$	0.23	-	-	W/A	
		$P_O = 8.5$ mW	0.13	-	-		
Peak Emission Wavelength	λ_p	$P_O = 8.5$ mW	NX6351GP27	1 260	-	1 280	nm
			NX6351GP29	1 280	-	1 300	
			NX6351GP31	1 300	-	1 320	
			NX6351GP33	1 320	-	1 340	
			NX6351GP35	1 340	-	1 360	
Side Mode Suppression Ratio	SMSR	$P_O = 8.5$ mW	35	-	-	dB	
Rise Time	t_r	20-80% *1	-	-	50	ps	
Fall Time	t_f	80-20% *1	-	-	50	ps	
Monitor Current	I_m	$V_R = 1.5$ V, $P_O = 8.5$ mW	100	-	1 000	μA	
Monitor Dark Current	I_D	$V_R = 3.3$ V, $T_C = 25^\circ\text{C}$	-	-	10	nA	
		$V_R = 3.3$ V	-	-	100		
Monitor PD Terminal Capacitance	C_t	$V_R = 3.3$ V, $f = 1$ MHz	-	-	20	pF	

Note: 1. 9.8304 Gb/s, PRBS 2³¹-1, NRZ, Duty Cycle = 50%

SAFETY INFORMATION ON THIS PRODUCT



SEMICONDUCTOR LASER



AVOID EXPOSURE-Invisible
 Laser Radiation is emitted from
 this aperture

<p>Warning Laser Beam</p>	<p>A laser beam is emitted from this diode during operation. The laser beam, visible or invisible, directly or indirectly, may cause injury to the eye or loss of eyesight.</p> <ul style="list-style-type: none"> • Do not look directly into the laser beam. • Avoid exposure to the laser beam, any reflected or collimated beam.
<p>Caution GaAs Products</p>	<p>This product uses gallium arsenide (GaAs). GaAs vapor and powder are hazardous to human health if inhaled or ingested, so please observe the following points.</p> <ul style="list-style-type: none"> • Follow related laws and ordinances when disposing of the product. If there are no applicable laws and/or ordinances, dispose of the product as recommended below. <ol style="list-style-type: none"> 1. Commission a disposal company able to (with a license to) collect, transport and dispose of materials that contain arsenic and other such industrial waste materials. 2. Exclude the product from general industrial waste and household garbage, and ensure that the product is controlled (as industrial waste subject to special control) up until final disposal. • Do not burn, destroy, cut, crush, or chemically dissolve the product. • Do not lick the product or in any way allow it to enter the mouth.

Revision History	NX6351GP Series Data Sheet
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Rev.	Date	Description	
		Page	Summary
1.00	Feb 25, 2013	-	First edition issued

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